

# Performance of an Imager Intensifier for IsCMOS Readout System of HERD

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# Outline

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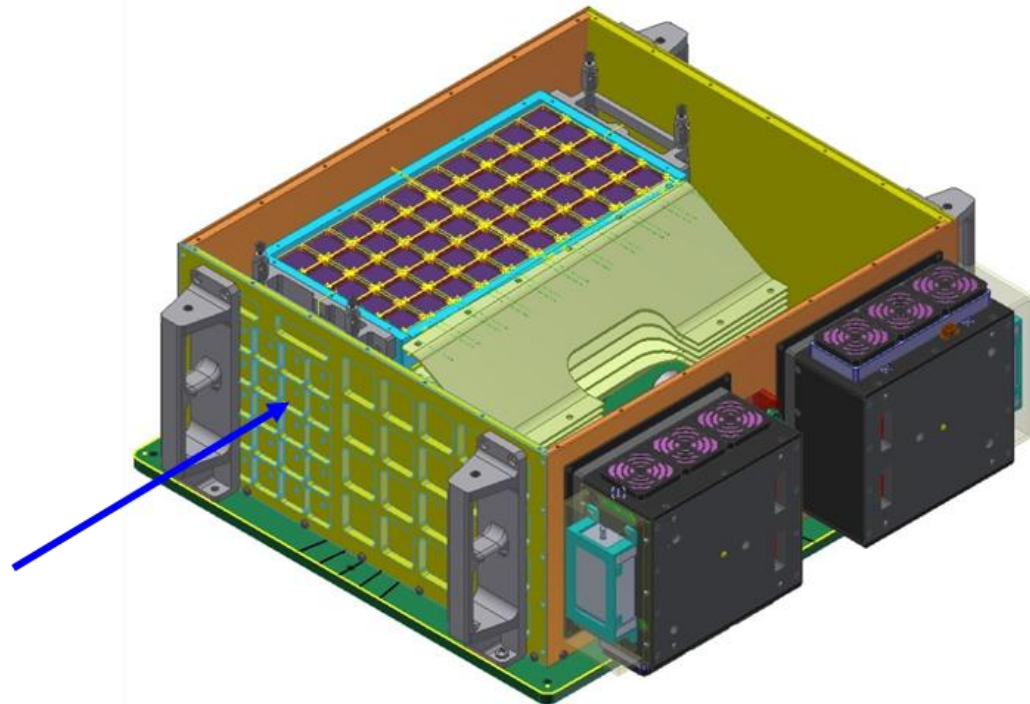


- System Concept and requirements
- Design and Results
- Summary

# Specifying Instrument requirements

- spectral response range: 450nm-600nm
- sensitivity: 0.3MIP/channel
- trigger off/on delay time:  $< 1\mu\text{s}$
- max frame rate: 500fps
- dynamic range:  $> 1000$

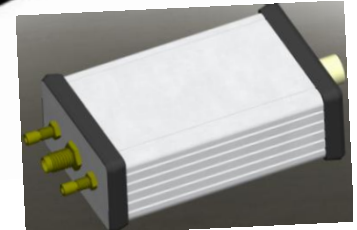
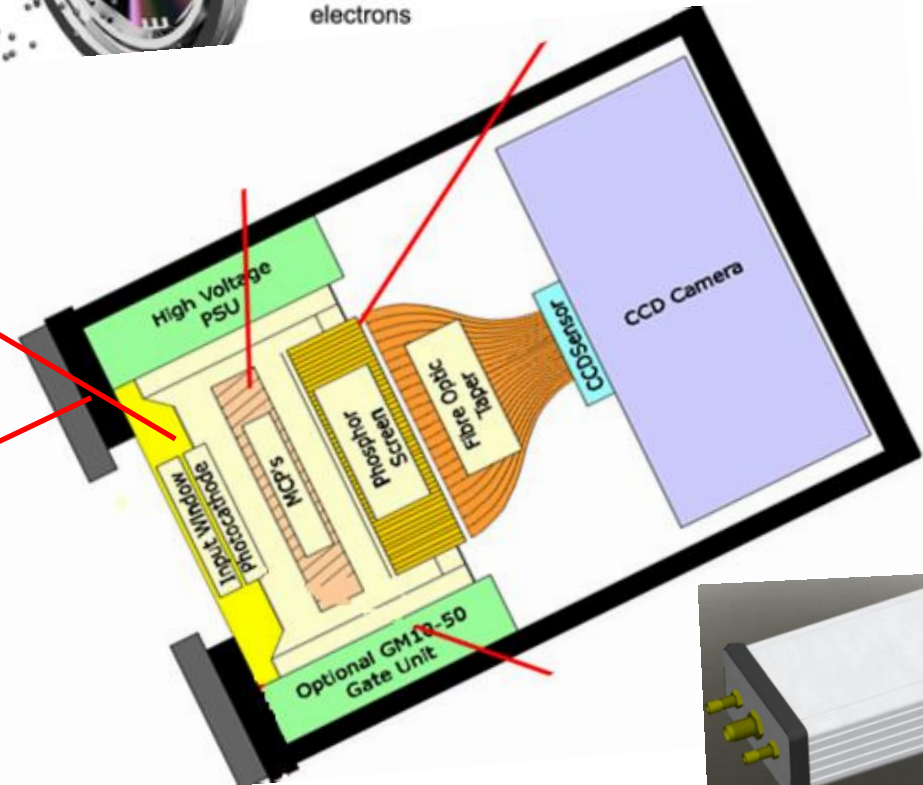
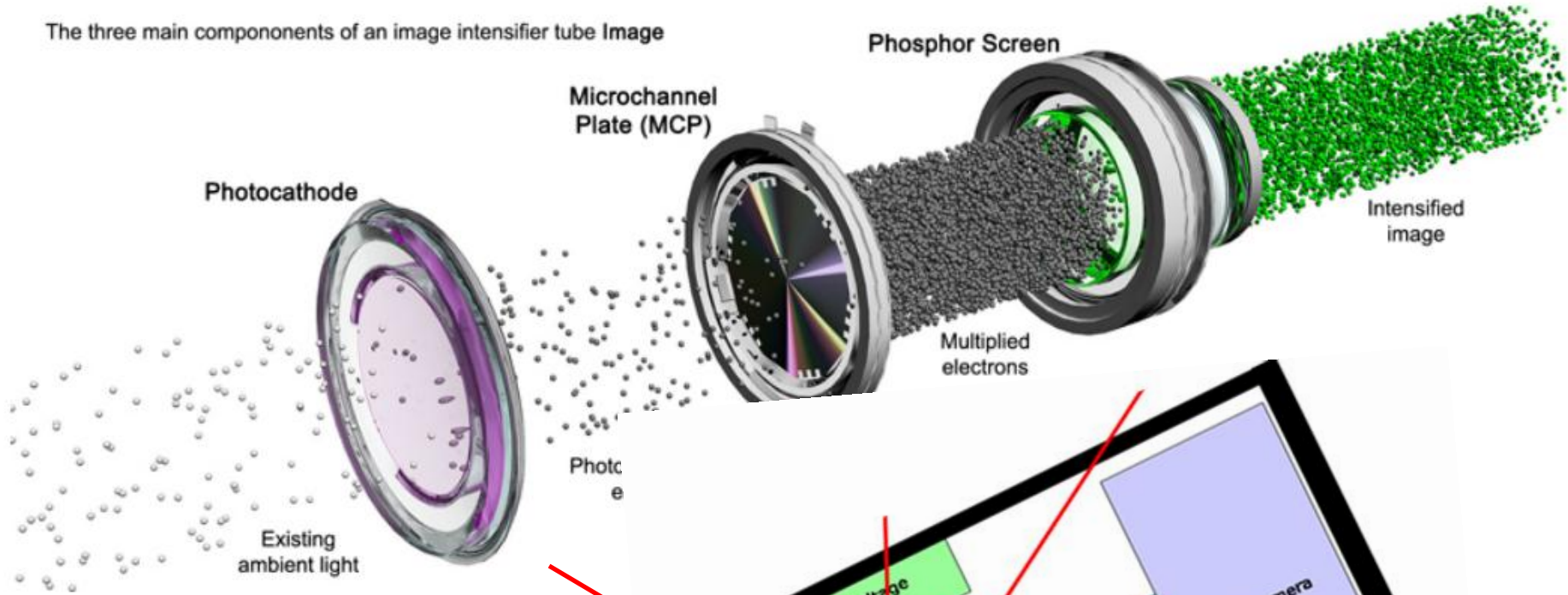
- 1 LYSO array
  - $5 \times 5 \times 10$  crystals
  - **2 IsCMOS systems**



# Optimize performance for finalizing IsCMOS design

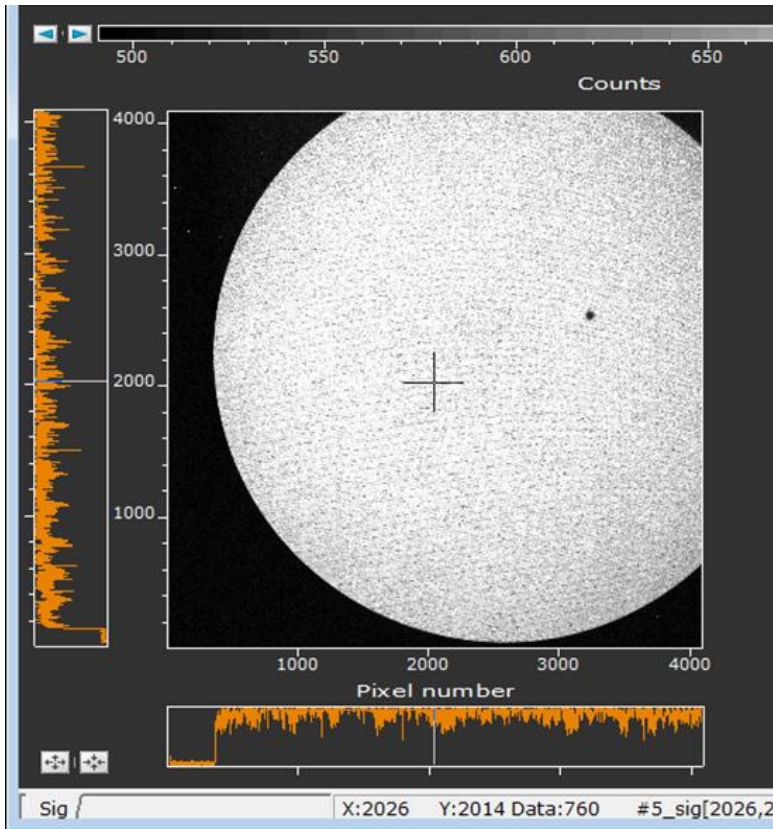


The three main components of an image intensifier tube Image

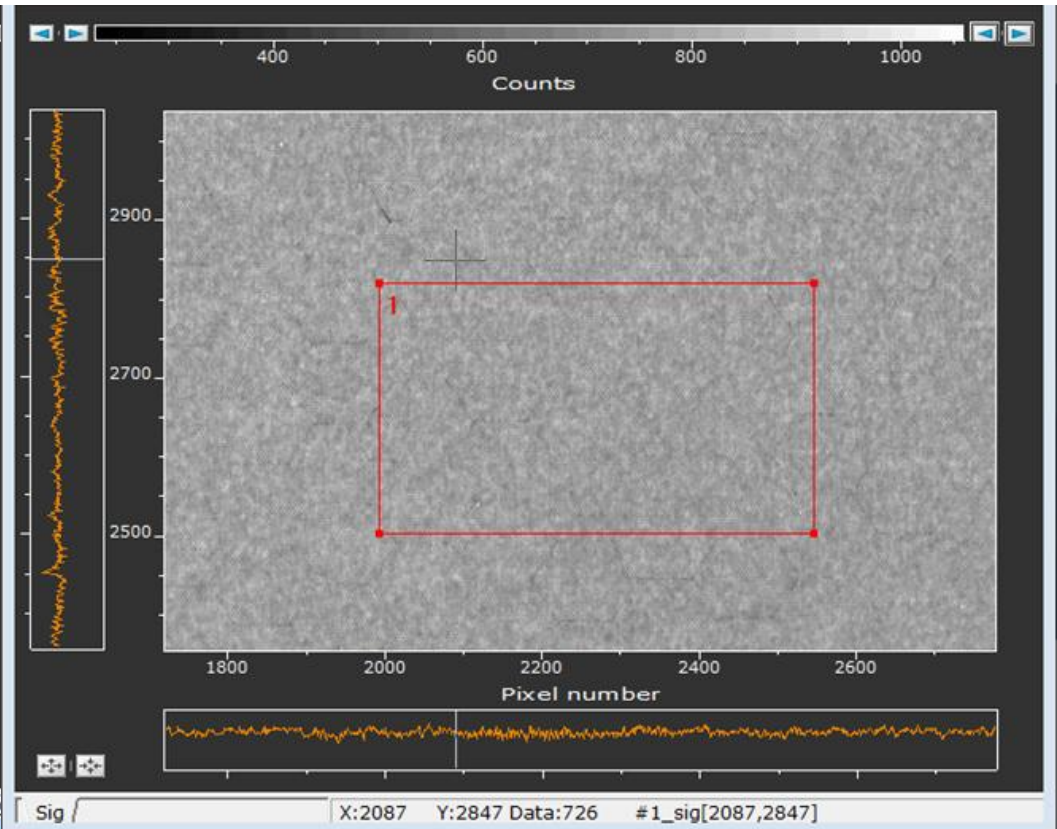


# Nonuniformity

Nonuniformity: 2.1%-5.2%



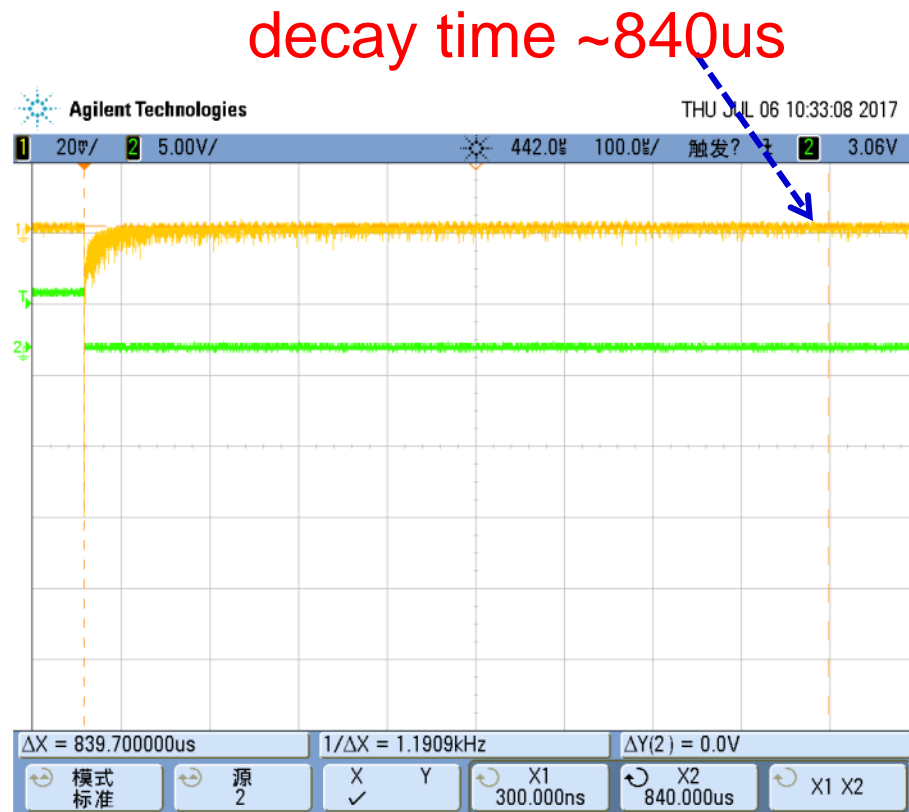
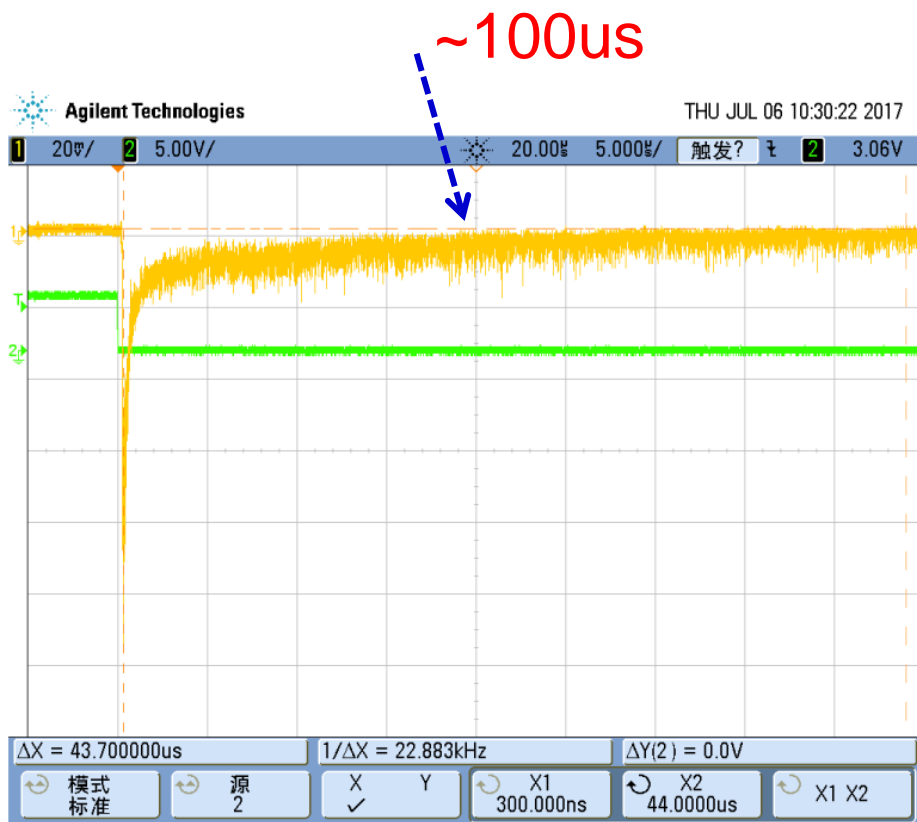
Overall picture



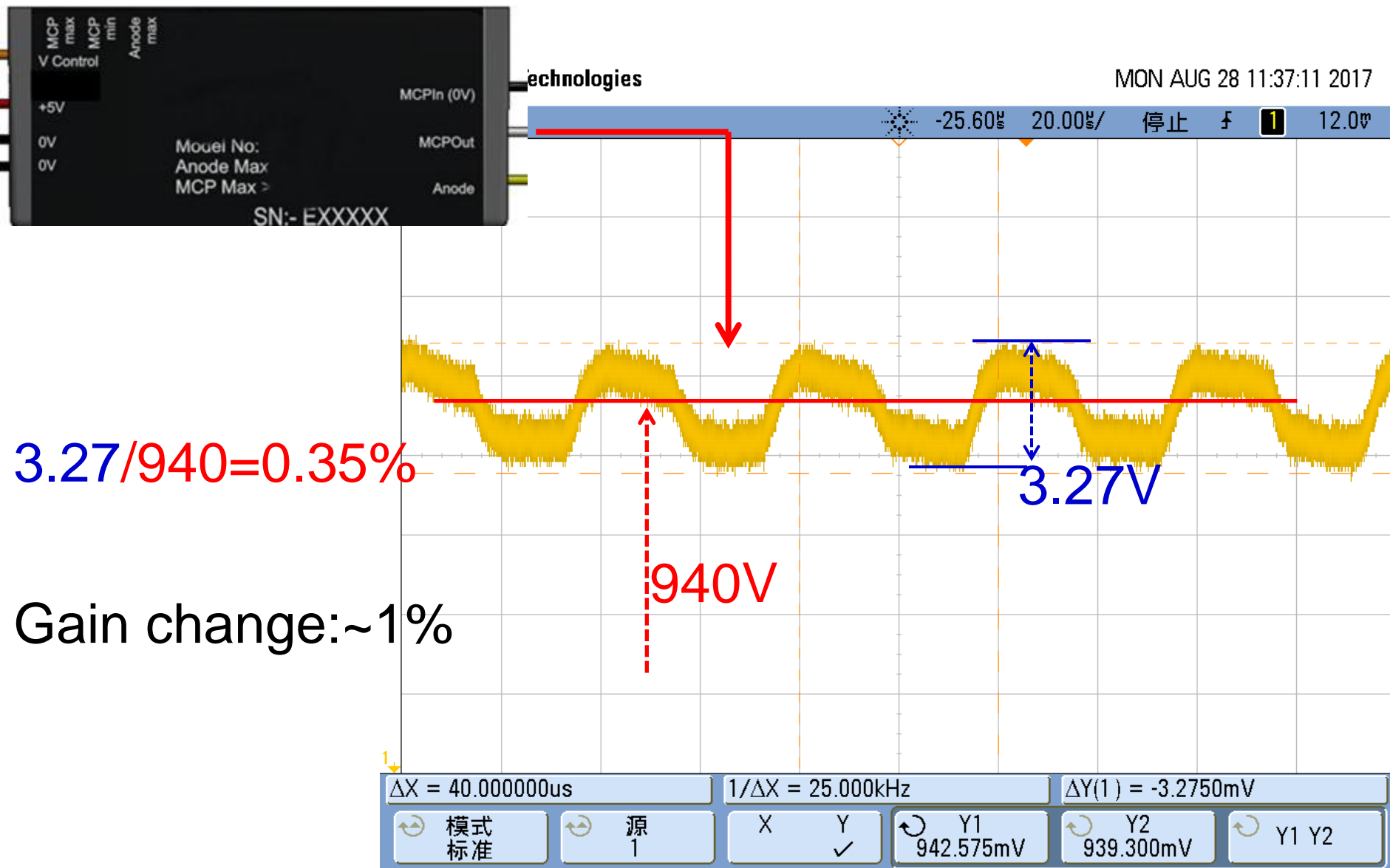
Partial magnification picture

# Phosphor screen: decay time

95% Energy is concentrated in 100us, and the 840us decay time match with sCMOS frame rate(500fps)



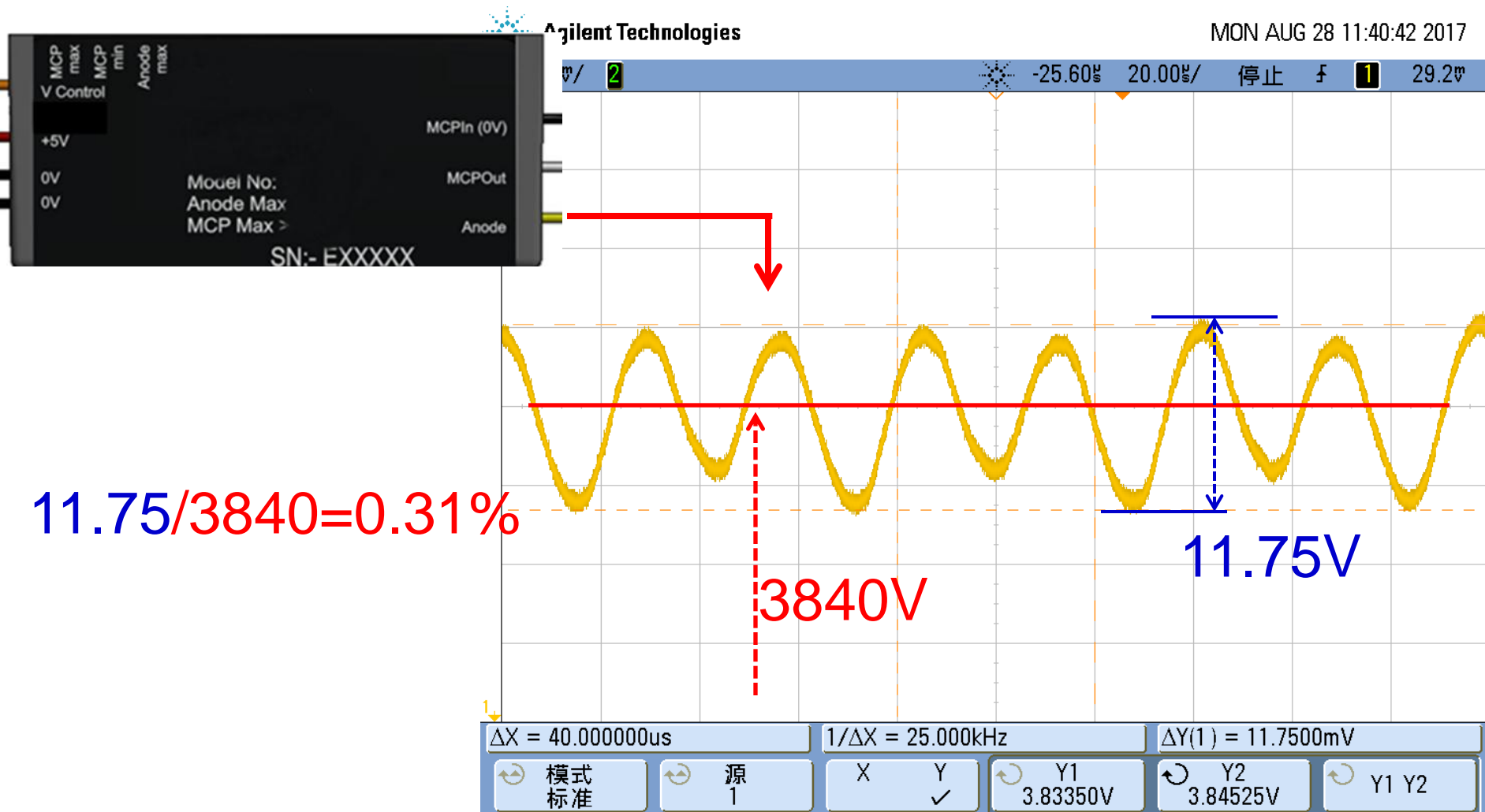
# High Voltage PSU: MCP gain



# High Voltage PSU: phosphor screen voltage

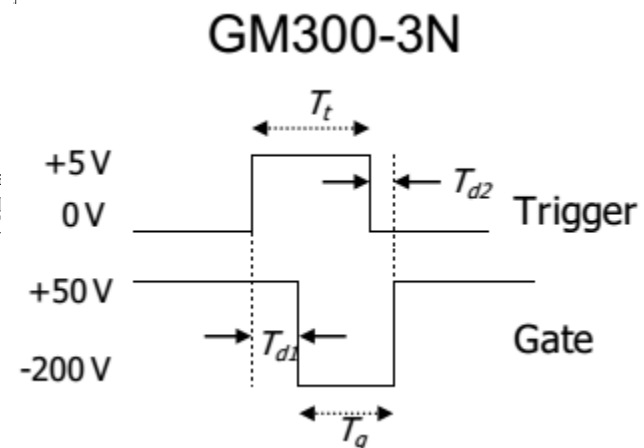
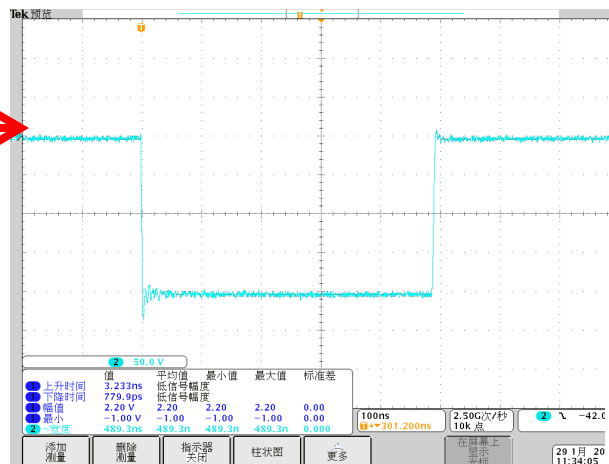
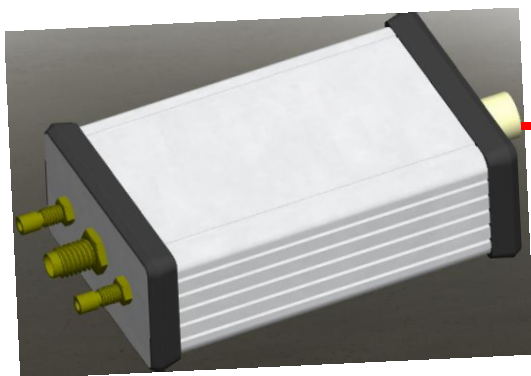


The effect on the brightness of the screen can be ignored





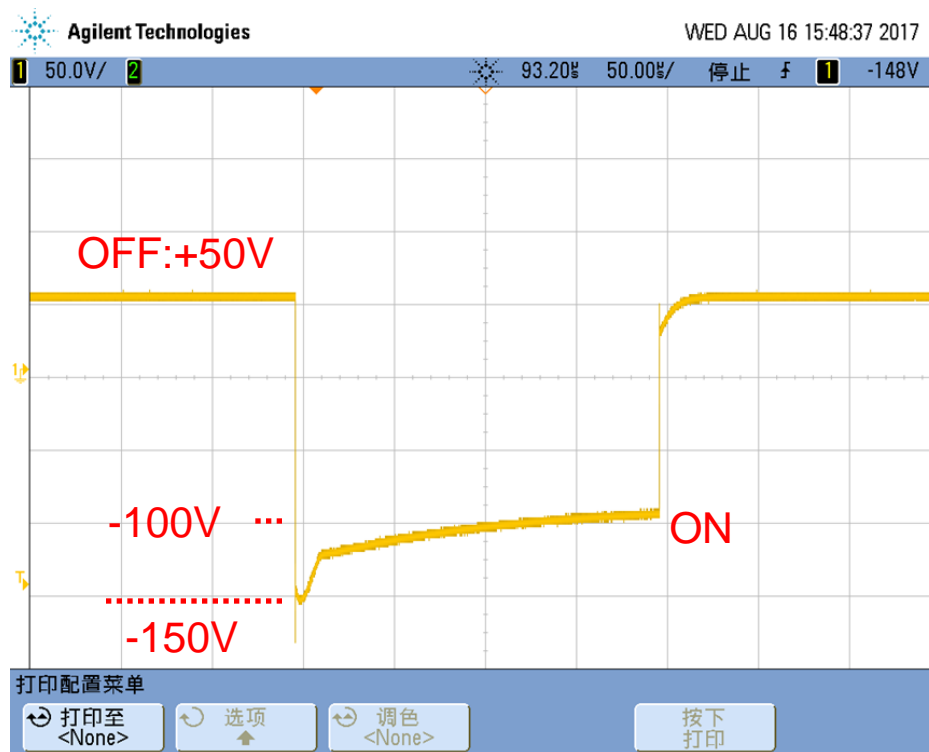
# Gated Unite for photocathode



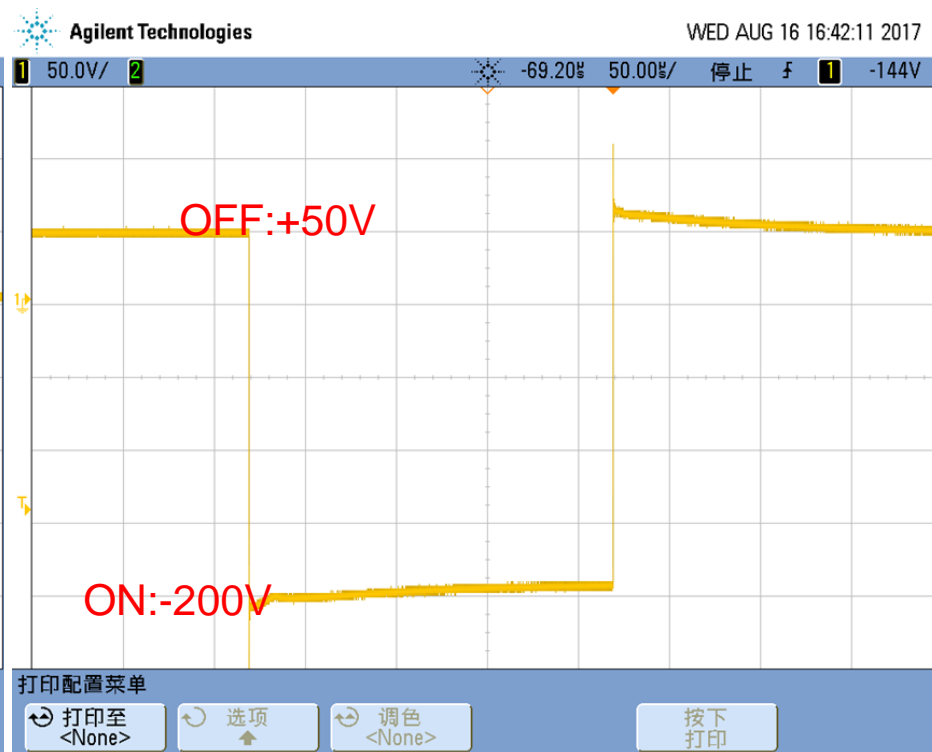
## Typical Timing Parameters

<b>Leading Edge Propagation Delay</b>	$T_{d1}$	50 ns
<b>Trailing Edge Propagation Delay</b>	$T_{d2}$	40 ns
<b>Trigger / Gate Offset Time <math>T_t - T_g</math></b>	$T_{d1} - T_{d2}$	10 ns
<b>Minimum Gate Width in Inverted Mode</b>	$T_g$	50 ns
<b>Propagation Delay Temperature Co-efficient</b>		40 ( $\pm 5$ ) ps / °C
<b>Gate Width Temperature Co-efficient</b>		$\pm 10$ ps / °C

# Gated Unite for photocathode



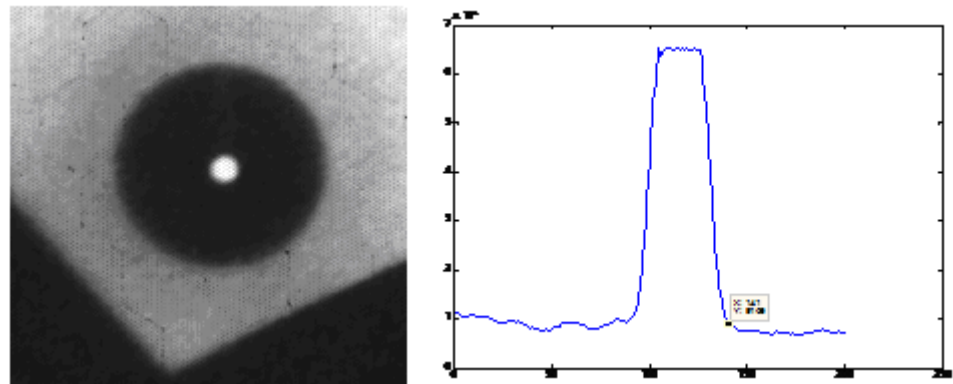
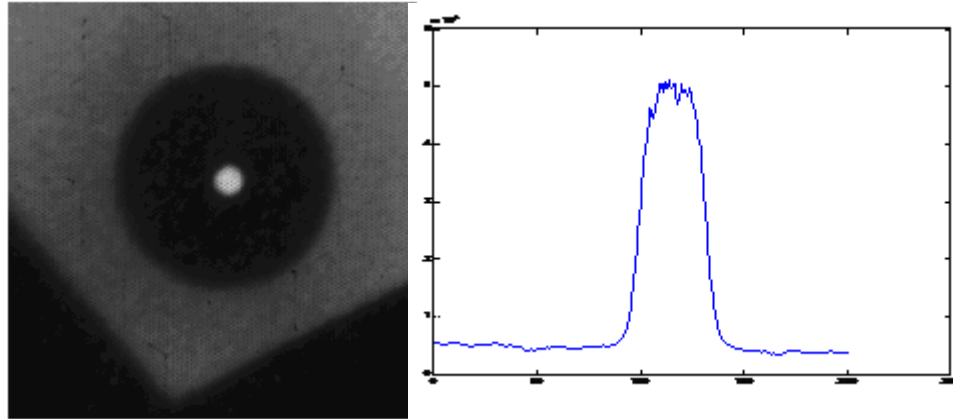
Impedance mismatching



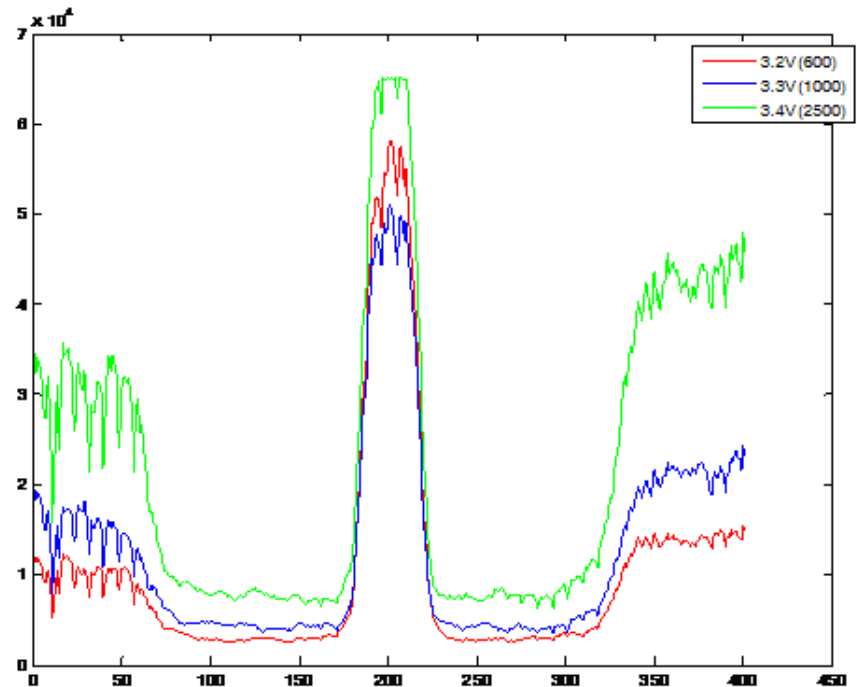
Impedance matching

# Spot Diffusion

## Test spot diffusion caused by different light intensity



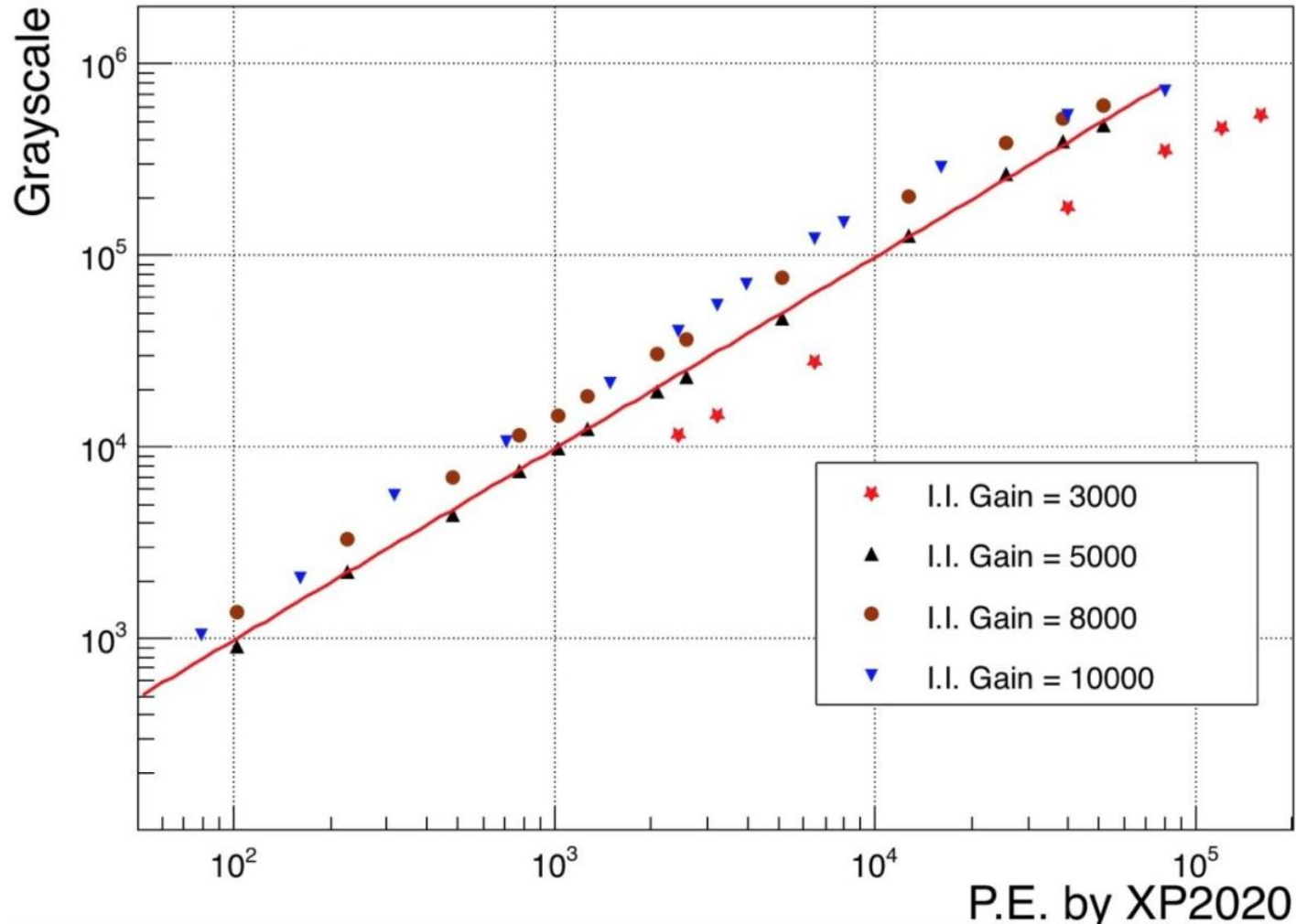
spot diffusion caused by I.I. is 1.5 times in different light intensity



spot diffusion caused by different gains of I.I.

# Dynamic range

sCMOS + 1 Taper + I.I.



**Dynamic range: 1000:1**

We have developed I.I. which satisfies most of our requirements

- sensitivity & trigger off/on delay time
- decay time

R&D is now focused on :Atomic layer deposition

- low noise photocathode
- lifetime and dynamic range improvement
- larger area detector



XIOPM

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***Thanks for your attention!***

# Atomic layer deposition (ALD)

Allows engineering of surfaces after MCP  
is fabricated-**high dynamic range & long lifetime**

- Optimize secondary electron coefficient for gain
- Optimize resistivity

Separates microchannel fabrication from  
surface preparation-**larger area detector**

- MCPs can be made from any glass, alumina, plastic
- Lithographic techniques for larger arrays of pores